# **Small Signal MOSFET**

-20 V, -760 mA, Single P-Channel, Gate Zener, SC-75, SC-89

#### Features

- Low R<sub>DS(on)</sub> for Higher Efficiency and Longer Battery Life
- Small Outline Package (1.6 x 1.6 mm)
- SC–75 Standard Gullwing Package
- ESD Protected Gate
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### Applications

- High Side Load Switch
- DC–DC Conversion
- Small Drive Circuits
- Battery Operated Systems such as Cell Phones, PDAs, Digital Cameras, etc.

#### **MAXIMUM RATINGS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise stated)

Parameter	Symbol	Value	Units	
Drain-to-Source Voltage	V <sub>DSS</sub>	-20	V	
Gate-to-Source Voltage	Gate-to-Source Voltage			V
Continuous Drain Current (Note 1)	· · · · · · · · · · · · · · · · · · ·		-760	mA
Power Dissipation (Note 1) SC-75 SC-89	SC–75 Steady State		301 313	mW
Pulsed Drain Current	Pulsed Drain Current tp =10 µs			mA
Operating Junction and Storage	T <sub>J</sub> , T <sub>STG</sub>	–55 to 150	°C	
Continuous Source Current (Bo	۱ <sub>S</sub>	-250	mA	
Lead Temperature for Soldering (1/8 in from case for 10 s)	ΤL	260	°C	
Gate-to-Source ESD Rating - (Human Body Model	, Method 3015)	ESD	1800	V

#### THERMAL RESISTANCE RATINGS

Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$		°C/W
SC-75		415	
SC-89		400	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

 Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

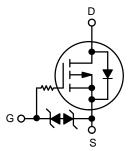


## **ON Semiconductor®**

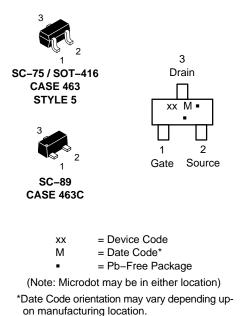
#### www.onsemi.com

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> TYP	I <sub>D</sub> MAX
	0.26 Ω @ -4.5 V	
–20 V	0.35 Ω @ −2.5 V	–760 mA
•	0.49 Ω @ –1.8 V	





MARKING DIAGRAM & PIN ASSIGNMENT



#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

#### ELECTRICAL CHARACTERISTICS (T<sub>.1</sub> = 25°C unless otherwise stated)

Parameter	Parameter Symbol Test Condition Min				Max	Unit
OFF CHARACTERISTICS			•			
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS}$ = 0 V, $I_D$ = -250 $\mu$ A	-20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V, V_{DS} = -16 V$		-1.0	-100	nA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = ±4.5 V		±1.0	±10	μΑ
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$	-0.45		-1.2	V
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -350 \text{ mA}$		0.26	0.36	Ω
		$V_{GS}$ = -2.5 V, I <sub>D</sub> = -300 mA		0.35	0.45	
		$V_{GS} = -1.8 \text{ V}, I_D = -150 \text{ mA}$		0.49	1.0	
Forward Transconductance	<b>g</b> fs	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -250 \text{ mA}$		0.4		S
CHARGES AND CAPACITANCES						
Input Capacitance	C <sub>ISS</sub>	$V_{GS} = 0 V, f = 1.0 MHz,$		156		pF
Output Capacitance	C <sub>OSS</sub>	$V_{DS} = -5.0 V$		28		
Reverse Transfer Capacitance	C <sub>RSS</sub>			18		
Total Gate Charge	Q <sub>G(TOT)</sub>	$V_{GS} = -4.5 \text{ V}, V_{DD} = -10 \text{ V},$ $I_{D} = -0.3 \text{ A}$		2.1		nC
Threshold Gate Charge	Q <sub>G(TH)</sub>	$I_{\rm D} = -0.3 \rm A$		0.125		
Gate-to-Source Charge	$Q_{GS}$			0.325		
Gate-to-Drain Charge	$Q_{GD}$			0.5		
SWITCHING CHARACTERISTICS (Note	3)					
Turn-On Delay Time	td <sub>(ON)</sub>	$V_{GS} = -4.5 \text{ V}, V_{DD} = -10 \text{ V},$		8.0		ns
Rise Time	t <sub>r</sub>	$I_D$ = -200 mA, $R_G$ = 10 $\Omega$		8.2		
Turn-Off Delay Time	td <sub>(OFF)</sub>			29		
Fall Time	t <sub>f</sub>	1		20.4		

Forward Diode Voltage	V <sub>SD</sub>	$V_{GS} = 0 V, I_{S} = -250 mA$	-0.72	-1.1	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test: pulse width  $\leq$  300 µs, duty cycle  $\leq$  2%.

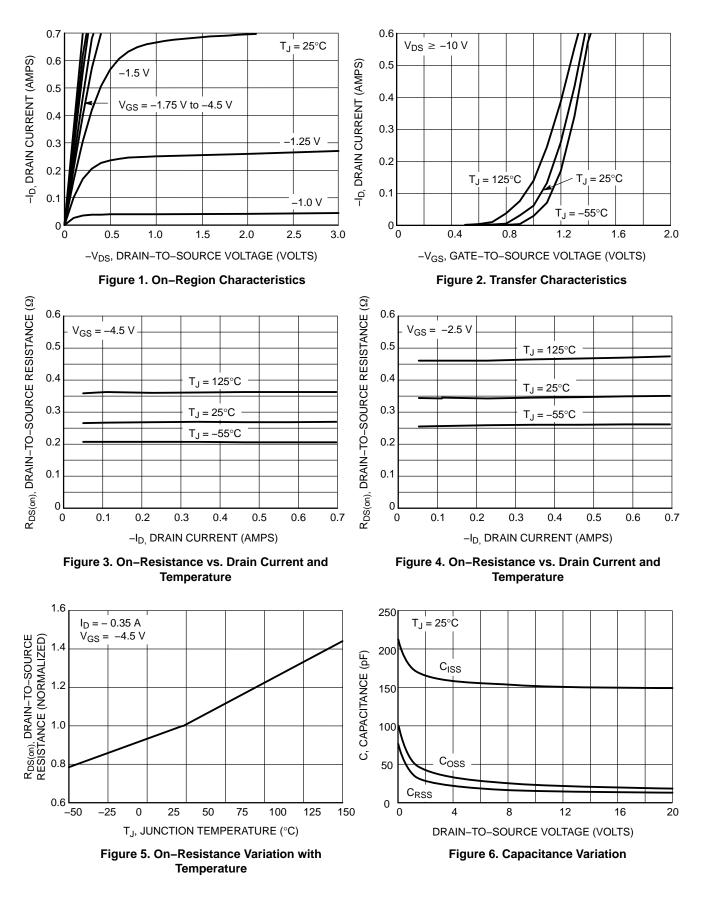
3. Switching characteristics are independent of operating junction temperatures.

#### **ORDERING INFORMATION**

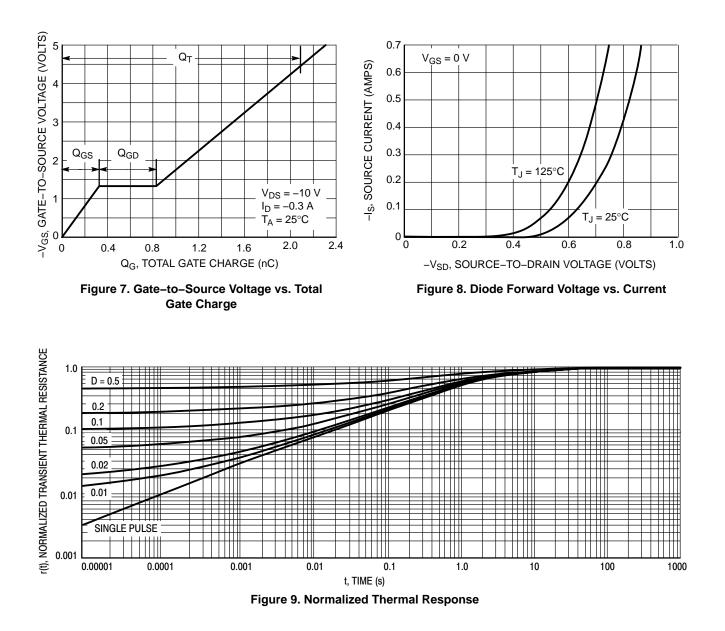
Device	Marking	Package	Shipping <sup>†</sup>
NTA4151PT1G	TN	SC-75 (Pb-Free)	3000 / Tape & Reel
NTE4151PT1G	ТМ	SC-89 (Pb-Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### **TYPICAL ELECTRICAL CHARACTERISTICS**

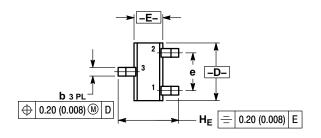


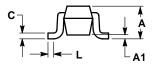
## **TYPICAL ELECTRICAL CHARACTERISTICS**



### PACKAGE DIMENSIONS

SC-75/SOT-416 CASE 463 **ISSUE F** 



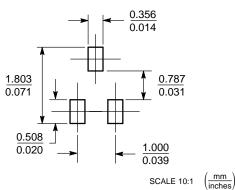


NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.70	0.80	0.90	0.027	0.031	0.035	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
b	0.15	0.20	0.30	0.006	0.008	0.012	
С	0.10	0.15	0.25	0.004	0.006	0.010	
D	1.55	1.60	1.65	0.059	0.063	0.067	
Е	0.70	0.80	0.90	0.027	0.031	0.035	
е	1.00 BSC			0	.04 BSC	)	
L	0.10	0.15	0.20	0.004	0.006	0.008	
HE	1.50	1.60	1.70	0.061	0.063	0.065	



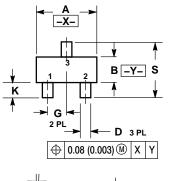
**SOLDERING FOOTPRINT\*** 

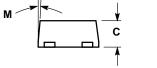


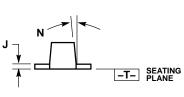
\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

SC-89, 3-LEAD CASE 463C-03 ISSUE C





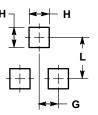


NOTES DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

- 3.
- CONTROLLING DIMENSION: MILLIMETERS MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 463C-01 OBSOLETE, NEW STANDARD 463C-02.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN NOM MAX		
Α	1.50	1.60	1.70	0.059	0.063	0.067
В	0.75	0.85	0.95	0.030	0.034	0.040
c	0.60	0.70	0.80	0.024	0.028	0.031
D	0.23	0.28	0.33	0.009	0.011	0.013
G	0.50 BSC			0.020 BSC		
Η	0.53 REF			0	.021 RE	F
L	0.10	0.15	0.20	0.004	0.006	0.008
к	0.30	0.40	0.50	0.012	0.016	0.020
L	1.10 REF			0.043 REF		
Μ			10			10
Ν			10			10
S	1.50	1.60	1.70	0.059	0.063	0.067

SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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